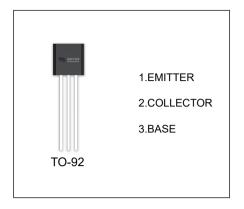


2SA673 TRANSISTOR (PNP)

FEATURES

- Low Frequency Amplifier
- Complementary Pair with 2SC1213



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SA673	TO-92	Bulk	1000pcs/Bag
2SA673-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-35	V
V _{CEO}	Collector-Emitter Voltage	-35	V
V _{EBO}	Emitter-Base Voltage	-4	V
Ic	Collector Current -Continuous	-0.5	Α
P _D	Collector Power Dissipation	400	mW
R ₀ JA	Thermal Resistance from Junction to Ambient	312	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-0.01mA,I _E =0	-35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA,I _B =0	-35			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.01mA,I _C =0	-4			٧
Collector cut-off current	I _{CBO}	V _{CB} =-20V,I _E =0			-0.5	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =-3V,I _C =0			-0.5	μΑ
DC current gain	h _{FE(1)}	V _{CE} =-3V, I _C =-10mA	60		320	
	h _{FE(2)} *	V _{CE} =-3V, I _C =-500mA	10			
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =-150mA,I _B =-15mA			-0.6	V
Base-emitter voltage	V _{BE}	V _{CE} =-3V, I _C =-10mA			-0.75	V

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.

CLASSIFICATION OF h_{FE(1)}

RANK	В	С	D	
RANGE	60-120	100-200	160-320	